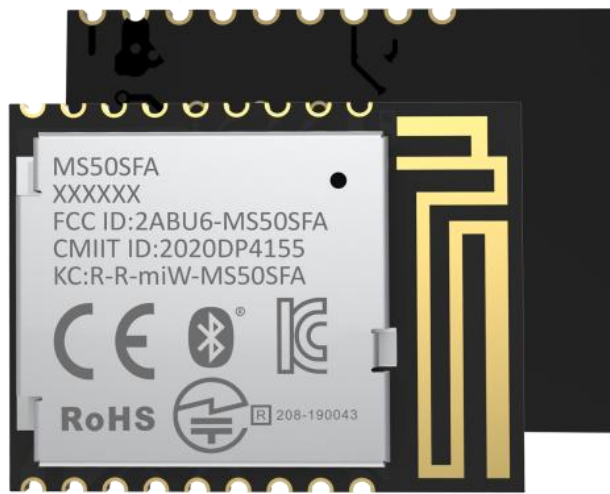


MINEWSEMI



MS50SFA

Bluetooth Low Energy module

Specification V1.0

Small-sized nRF52832 Module MS50SFA Specification



MS50SFA is a compact (15.8 x 12.0 x 2.0 mm), highly flexible, ultra-low power wireless BLE 5.0 Module based on nRF52832 SoCs; Its powerful 32-bit ARM Cortex™ M4F CPU, a 512KB flash memory, a 64 KB RAM and integrating a 2.4 GHz transceiver can offer the perfect solution for Bluetooth connectivity.

Features

1. Frequency: 2400 to 2483 MHz
2. Max. Output power: +4dBm
3. Single power supply: 1.7 – 3.6V
4. Range: up to 60 meters in open space
5. Chip: nRF52832 (Nordic)
6. GPIO Quantity: 13
7. 512KB Flash and 64KB RAM (nRF52832)
8. Module size: 15.8 x 12.0 x 2.0 mm
9. ARM Cortex-M4F processor
10. Metal shielding with marking
11. UART communication protocol (Slave \Master)
12. Antenna: PCB,Ceramic
13. Operating Temperature range: -40 to 85 degree Celsius

Application

1. Medical devices
2. Heart rate monitor
3. Blood pressure monitor
4. Blood glucose meter
5. Thermometer
6. Sport facilities
7. Weighing machine
8. Sports and fitness sensors
9. Accessories
10. 3D glasses and gaming controller
11. Mobile accessories
12. Remote controllers / Toys
13. Electronic devices
14. Cycle computer

INDEX

1 Product Introduction	- 4 -
1.1 Ordering information	- 4 -
2 Pin Description	- 5 -
2.1 Pin assignment	- 5 -
2.1.1 MS50SFA PCB Antenna	- 5 -
2.1.2 MS50SFA chip Antenna	- 5 -
2.2 Pin definition	- 6 -
2.3 Block diagram	- 7 -
2.4 Mechanical Drawing	- 8 -
2.4.1 MS50SFA PCB Antenna	- 8 -
2.4.2 MS50SFA chip Antenna	- 8 -
3 Electrical Specification	- 9 -
3.1 Absolute maximum ratings	- 9 -
3.2 Recommended operating conditions	- 10 -
3.3 Electronic characteristic	- 10 -
3.3.1 General radio characteristics	- 10 -
3.3.2 Radio current consumption (Transmitter)	- 11 -
3.3.3 Radio current consumption (Transmitter)	- 12 -
3.3.4 Radio current consumption (Receiver)	- 13 -
3.3.5 Transmitter specification	- 13 -
3.3.6 Receiver operation	- 14 -
3.3.7 RX selectivity	- 15 -
3.3.8 RX intermodulation	- 16 -
3.3.9 Radio timing	- 17 -
3.3.10 Received signal strength indicator (RSSI) specifications	- 18 -
4 Electrical Schematic	- 19 -
5 Package Information	- 20 -
5.1 Package dimension	- 20 -
5.2 Mark on metal shield	- 21 -
6 Reflow and Soldering	- 22 -
7 Certification	- 23 -
7.1 CE Certification	- 23 -
7.2 FCC Certification	- 23 -
7.3 Full Bluetooth Declaration ID	- 24 -
7.4 Japan (TELEC)	- 24 -
7.5 KC	- 24 -
7.6 Environmental	- 24 -
7.7 RoHs	- 24 -
7.8 Reach	- 24 -
8 Notes & Cautions	- 25 -
8.1 Design notes	- 25 -
8.2 Layout notes	- 25 -
8.3 Installation and soldering	- 26 -
8.4 Handling and storage	- 26 -
8.5 Life support applications	- 27 -
9 Disclaimer	- 28 -
Revision History	- 28 -
COPYRIGHT STATEMENT	- 29 -

1 Product Introduction

MS50SFA is a compact (15.8 x 12.0 x 2.0 mm), highly flexible, ultra-low power wireless BLE 5.0 Module based on nRF52810 SoCs; Its powerful 32-bit ARM Cortex™ M4 CPU, a 192KB Flash memory, a 24KB RAM and integrating a 2.4 GHz transceiver can offer the perfect solution for Bluetooth connectivity.

MS50SFA can meet the most demanding applications, it allows faster time to market with high performance, low power management and reduced development cost. Also, its range is estimated up to 60 meters in open space.

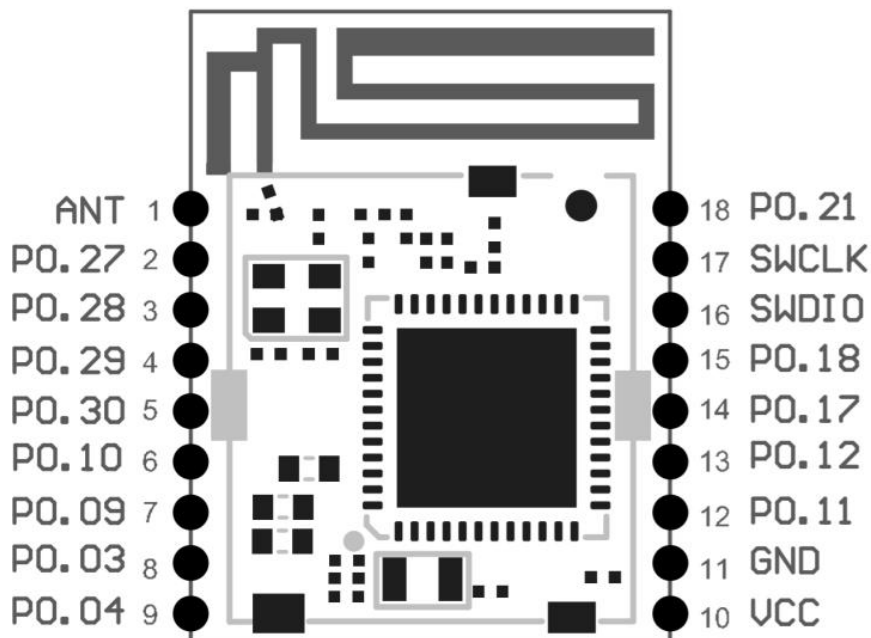
1.1 Ordering information

Ordering number	Description
MS50SFA-1Y10AIR	nRF52832-QFAA BT 5.0 Module, PCB Antenna, Reel pack
MS50SFA-2Y10AIR	nRF52832-QFAA BT 5.0 Module, Ceramic Antenna, Reel pack

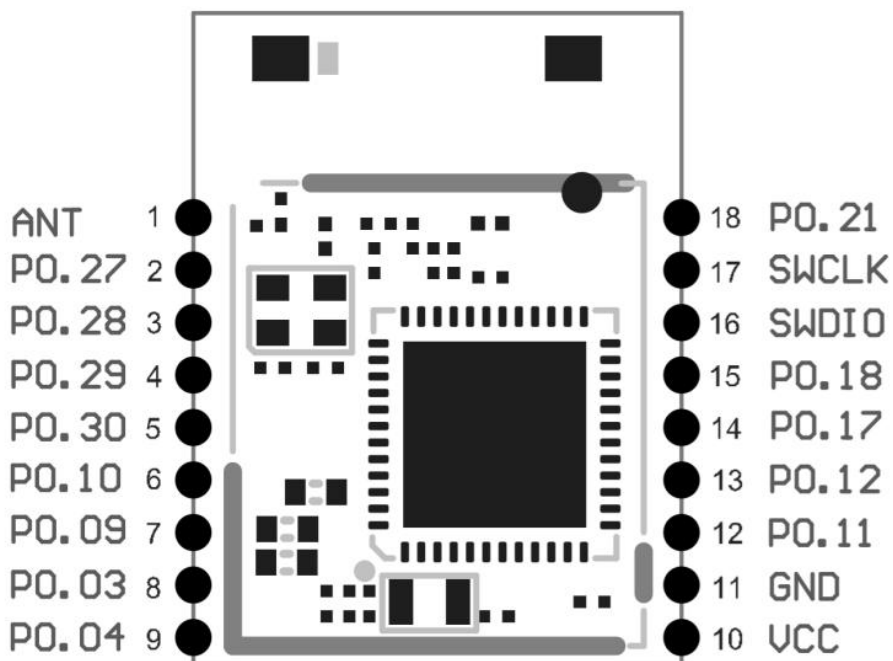
2 Pin Description

2.1 Pin assignment

2.1.1 MS50SFA PCB Antenna



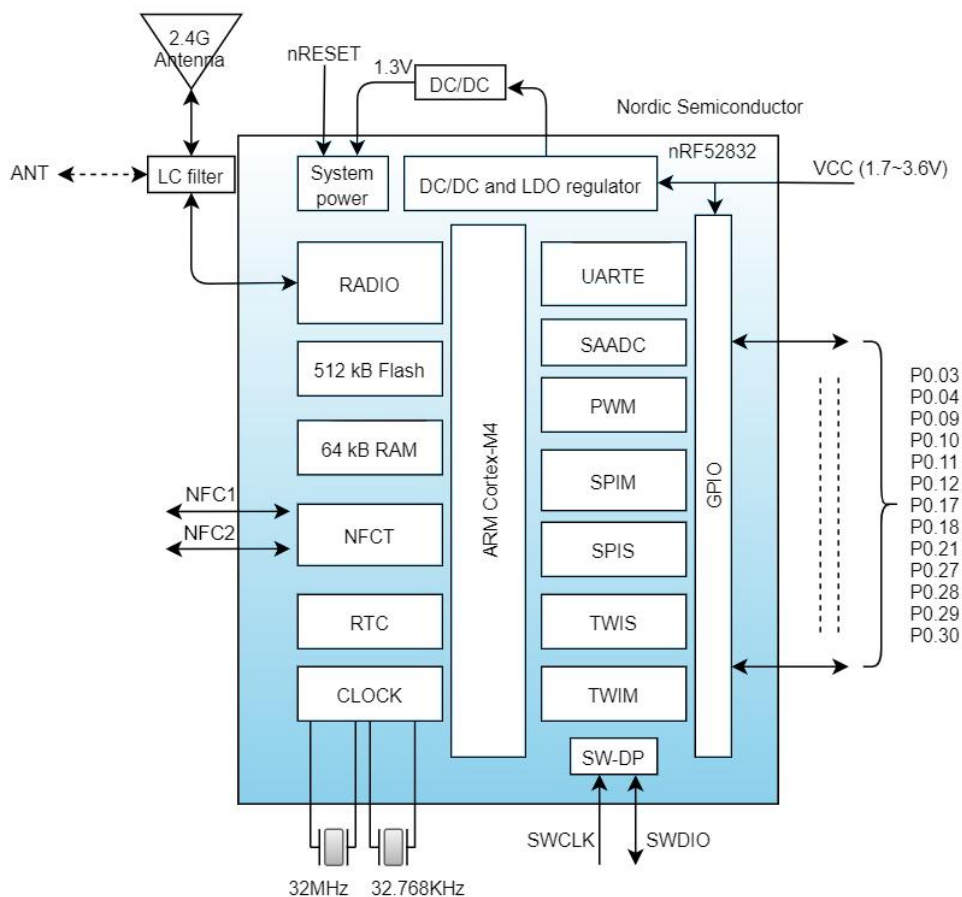
2.1.2 MS50SFA chip Antenna



2.2 Pin definition

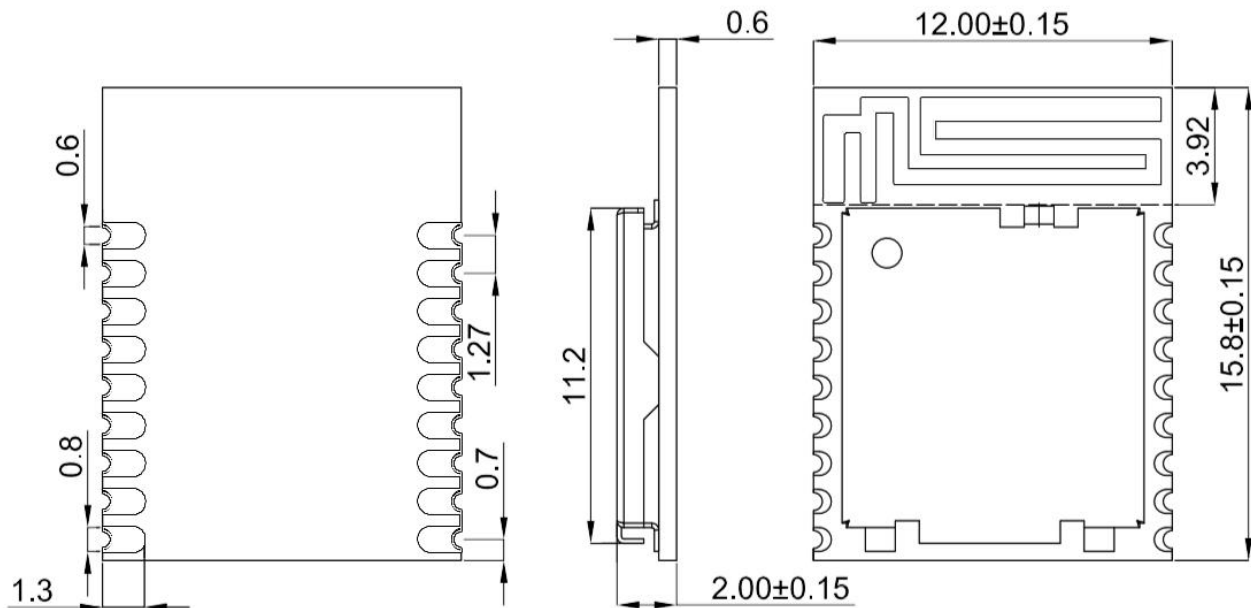
Symbol	Definition	Description	Notes
VCC	Power positive pole		
GND	Power negative pole		
P0.04	BRX	UART receive	RX of Bluetooth module
P0.03	BTX	UART transmit	TX of Bluetooth module
P0.17	SLP	Sleep/arouse	Sleep is high electrical level, arouse is low electrical level Sleep condition(low electrical level), idle condition(flicker once a second, that is, 800ms high electrical lever, 200ms is low electrical lever in circle), working condition(high electrical level); Idle condition: broadcasting condition; Working condition: The module have connected with the device.
P0.11	LED1	Indicator lighting	
P0.18	BTDATA	Host device send data	As the request of sending data(used in wake up the module). 0:host device send the data, module will waiting for receiving the data from host device, module will not sleep in this time. 1:host device have no data to send or finished the data sending, the module should place this signal line in 1.
P0.12	FIFO-FULL	Transmission space is full	How to judge a transmission space is ready to use. 0: Bluetooth module have available space to use and ready to transmission. 1: host device stop transmitting and waiting for the available space.

2.3 Block diagram

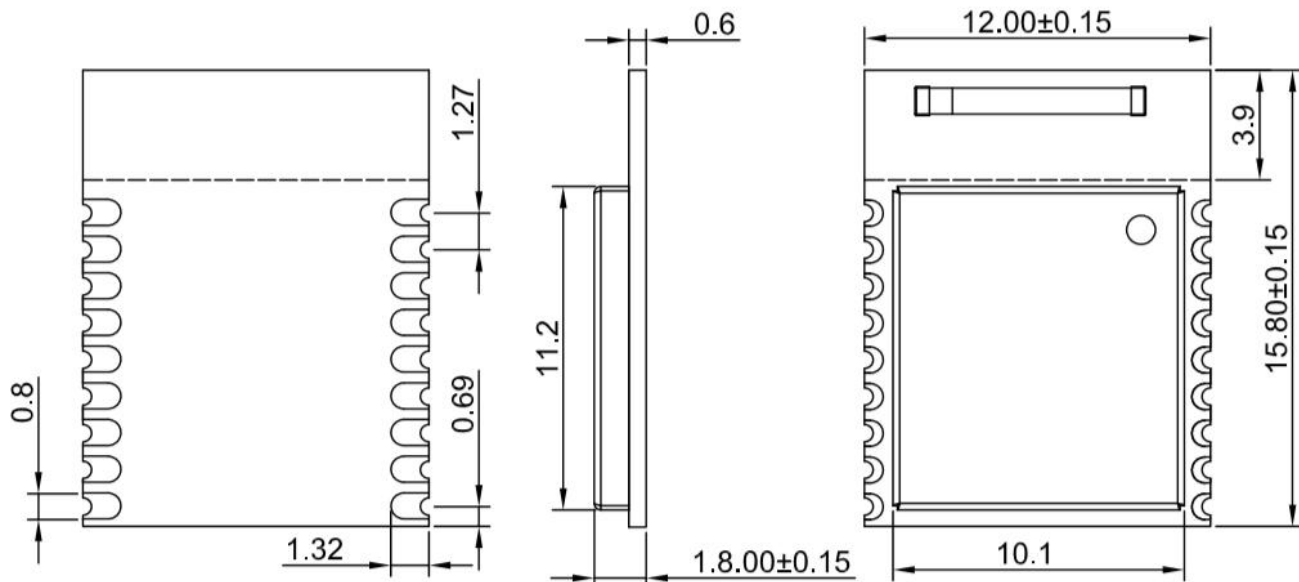


2.4 Mechanical Drawing

2.4.1 MS50SFA PCB Antenna



2.4.2 MS50SFA chip Antenna



Important: Unit: mm Tolerance: +/- 0.1, default
Recommend solder pad size: 1.8*0.8mm, solder pad is suggested to extend 0.5mm distance.

3 Electrical Specification

The electrical specifications of the module are directly related to the Nordic semiconductor Specifications for the nRF52832 chipset. The below information is only the extract from nRF52832 specification. For more detailed information, please refer to the up-to-date specification of the chipset available on the Nordic semiconductor website.

3.1 Absolute maximum ratings

Note	Min.	Max.	Unit
Supply voltages			
VDD	-0.3	+3.9	V
VSS		0	V
I/O pin voltage			
$V_{I/O}, VDD \leq 3.6\text{ V}$	-0.3	VDD+0.3V	V
$V_{I/O}, VDD > 3.6\text{ V}$	-0.3	3.9V	V
Environmental WLCSP package			
Storage temperature	-40	+125	°C
MSL(moisture sensitivity level)		1	
ESD HBM(Human Body Model)		3	kV
ESD HBM Class(Human Body Model Class)		2	
ESD CDM(Charged Device Model)		1	kV
Flash Memory			
Endurance	10 000		write/erase cycles
Retention at 85 °C	10		years

Important: Maximum ratings are the extreme limits to which the chip can be exposed for a limited amount of time without permanently damaging it. Exposure to absolute maximum ratings for prolonged periods of time may affect the reliability of the device.

3.2 Recommended operating conditions

The operating conditions are the physical parameters that the chip can operate within.

Symbol	Parameter	Notes	Min.	Nom.	Max.	Units
VDD	Supply voltage, independent of DCDC enable		1.7	3.0	3.6	V
T _{R,VDD}	Supply rise time (0 V to 1.7 V)				60	ms
TA	Operating temperature		-40	25	85	°C

Important: The on-chip power-on reset circuitry may not function properly for rise times longer than the specified maximum.

3.3 Electronic characteristic

3.3.1 General radio characteristics

Symbol	Description	Min.	Typ.	Max.	Units
f _{OP}	Operating frequencies	2360		2500	MHz
f _{PLL,CH,SP}	PLL channel spacing		1		MHz
f _{DELTA,1M}	Frequency deviation @ 1 Msps		±170		kHz
f _{DELTA,BLE,1M}	Frequency deviation @ BLE 1 Msps		±250		kHz
f _{DELTA,2M}	Frequency deviation @ 2 Msps		±320		kHz
f _{DELTA,BLE,2M}	Frequency deviation @ BLE 2 Msps		±500		kHz
Fsk _{BPS}	On-the-air data rate	1000		2000	ksps

3.3.2 Radio current consumption (Transmitter)

Symbol	Description	Min.	Typ.	Max.	Units
$I_{TX,PLUS4dBm,DCDC}$	TX only run current(DCDC,3V) $P_{RF}=+4$ dBm		7.5		mA
$I_{TX,PLUS4dBm}$	TX only run current $P_{RF}=+4$ dBm		16.6		mA
$I_{TX,0dBm,DCDC}$	TX only run current(DCDC,3V) $P_{RF}=0$ dBm		5.3		mA
$I_{TX,0dBm}$	TX only run current $P_{RF}=0$ dBm		11.6		mA
$I_{TX,MINUS4dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-4$ dBm		4.2		mA
$I_{TX,MINUS4dBm}$	TX only run current $P_{RF}=-4$ dBm		9.3		mA
$I_{TX,MINUS8dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-8$ dBm		3.8		mA
$I_{TX,MINUS8dBm}$	TX only run current $P_{RF}=-8$ dBm		8.4		mA
$I_{TX,MINUS12dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-12$ dBm		3.5		mA
$I_{TX,MINUS12dBm}$	TX only run current $P_{RF}=-12$ dBm		7.7		mA
$I_{TX,MINUS16dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-16$ dBm		3.3		mA
$I_{TX,MINUS16dBm}$	TX only run current $P_{RF}=-16$ dBm		7.3		mA
$I_{TX,MINUS20dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-20$ dBm		3.2		mA
$I_{TX,MINUS20dBm}$	TX only run current $P_{RF}=-20$ dBm		7.0		mA
$I_{TX,MINUS40dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-40$ dBm		2.7		mA
$I_{TX,MINUS40dBm}$	TX only run current $P_{RF}=-40$ dBm		5.9		mA
$I_{START,TX,DCDC}$	TX start-up current DCDC,3V $P_{RF}=4$ dBm		4.0		mA
$I_{START,TX}$	TX start-up current $P_{RF}=4$ dBm		8.8		mA

3.3.3 Radio current consumption (Transmitter)

Symbol	Description	Min.	Typ.	Max.	Units
$I_{TX,PLUS4dBm,DCDC}$	TX only run current(DCDC,3V) $P_{RF}=+4$ dBm		7.5		mA
$I_{TX,PLUS4dBm}$	TX only run current $P_{RF}=+4$ dBm		16.6		mA
$I_{TX,0dBm,DCDC}$	TX only run current(DCDC,3V) $P_{RF}=0$ dBm		5.3		mA
$I_{TX,0dBm}$	TX only run current $P_{RF}=0$ dBm		11.6		mA
$I_{TX,MINUS4dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-4$ dBm		4.2		mA
$I_{TX,MINUS4dBm}$	TX only run current $P_{RF}=-4$ dBm		9.3		mA
$I_{TX,MINUS8dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-8$ dBm		3.8		mA
$I_{TX,MINUS8dBm}$	TX only run current $P_{RF}=-8$ dBm		8.4		mA
$I_{TX,MINUS12dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-12$ dBm		3.5		mA
$I_{TX,MINUS12dBm}$	TX only run current $P_{RF}=-12$ dBm		7.7		mA
$I_{TX,MINUS16dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-16$ dBm		3.3		mA
$I_{TX,MINUS16dBm}$	TX only run current $P_{RF}=-16$ dBm		7.3		mA
$I_{TX,MINUS20dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-20$ dBm		3.2		mA
$I_{TX,MINUS20dBm}$	TX only run current $P_{RF}=-20$ dBm		7.0		mA
$I_{TX,MINUS40dBm,DCDC}$	TX only run current DCDC,3V $P_{RF}=-40$ dBm		2.7		mA
$I_{TX,MINUS40dBm}$	TX only run current $P_{RF}=-40$ dBm		5.9		mA
$I_{START,TX,DCDC}$	TX only run current DCDC,3V $P_{RF}=4$ dBm		4.0		mA
$I_{START,TX}$	TX only run current $P_{RF}=4$ dBm		8.8		mA

3.3.4 Radio current consumption (Receiver)

Symbol	Description	Min.	Typ.	Max.	Units
$I_{RX,1M,DCDC}$	RX only run current (DCDC, 3V) 1Msps / 1Msps BLE		5.4		mA
$I_{RX,1M}$	RX only run current 1Msps / 1Msps BLE		11.7		mA
$I_{RX,2M,DCDC}$	RX only run current (DCDC, 3V) 2Msps / 2Msps BLE		5.8		mA
$I_{RX,2M}$	RX only run current 2Msps / 2Msps BLE		12.9		mA
$I_{START,RX,DCDC}$	RX start-up current (DCDC 3V)		3.5		mA
$I_{START,RX,LDO}$	RX start-up current (LDO 3V)		7.5		mA

3.3.5 Transmitter specification

Symbol	Description	Min.	Typ.	Max.	Units
P_{RF}	Maximum output power		4	6	dBm
P_{RFC}	RF power control range		24		dB
P_{RFCR}	RF power accuracy			±4	dB
$P_{RF1,1}$	1st Adjacent Channel Transmit Power 1 MHz (1 Msps Nordic proprietary mode)		-25		dBc
$P_{RF2,1}$	2nd Adjacent Channel Transmit Power 2 MHz (1 Msps Nordic proprietary mode)		-50		dBc
$P_{RF1,2}$	1st Adjacent Channel Transmit Power 2 MHz (2 Msps Nordic proprietary mode)		-25		dBc
$P_{RF2,2}$	2nd Adjacent Channel Transmit Power 4 MHz (2 Msps Nordic proprietary mode)		-50		dBc
$P_{RF1,2,BLE}$	1st Adjacent Channel Transmit Power 2 MHz (2 Msps BLE mode)		-20		dBc
$P_{RF2,2,BLE}$	2nd Adjacent Channel Transmit Power 4 MHz (2 Msps BLE mode)		-50		dBc

3.3.6 Receiver operation

Symbol	Description	Min.	Typ.	Max.	Units
$P_{RX,MAX}$	Maximum received signal strength at < 0.1% BER		0		dBm
$P_{SENS,IT,1M}$	Sensitivity, 1Msps nRF mode ¹		-93		dBm
$P_{SENS,IT,SP,1M,BLE}$	Sensitivity, 1Msps BLE ideal transmitter, <=37 bytes BER=1E-3 ²		-96		dBm
$P_{SENS,IT,LP,1M,BLE}$	Sensitivity, 1Msps BLE ideal transmitter >=128 bytes BER=1E-4 ³		-95		dBm
$P_{SENS,IT,2M}$	Sensitivity, 2Msps nRF mode ⁴		-89		dBm
$P_{SENS,IT,SP,2M,BLE}$	Sensitivity, 2Msps BLE ideal transmitter, Packet length<=37bytes		-93		dBm
$P_{SENS,DT,SP,2M,BLE}$	Sensitivity, 2Msps BLE dirty transmitter, Packet length<=37bytes		-93		dBm
$P_{SENS,IT,LP,2M,BLE}$	Sensitivity, 2Msps BLE ideal transmitter >= 128bytes		-92		dBm
$P_{SENS,DT,LP,2M,BLE}$	Sensitivity, 2Msps BLE dirty transmitter, Packet length >= 128bytes		-92		dBm

¹ Typical sensitivity applies when ADDR0 is used for receiver address correlation. When ADDR[1...7] are used for receiver address correlation, the typical sensitivity for this mode is degraded by 3dB.

² As defined in the Bluetooth Core Specification v4.0 Volume 6: Core System Package (Low Energy Controller Volume)

³ Equivalent BER limit < 10E-04

⁴ Desired signal level at PIN = -67 dBm. One interferer is used, having equal modulation as the desired signal. The input power of the interferer where the sensitivity equals BER = 0.1% is presented.

3.3.7 RX selectivity

Symbol	Description	Min.	Typ.	Max.	Units
$C/I_{1M,co-channel}$	1Mpsps mode, Co-Channel interference		9		dBm
$C/I_{1M,-1MHz}$	1 Mpsps mode, Adjacent (-1 MHz) interference		-2		dBm
$C/I_{1M,+1MHz}$	1 Mpsps mode, Adjacent (+1 MHz) interference		-10		dBm
$C/I_{1M,-2MHz}$	1 Mpsps mode, Adjacent (-2 MHz) interference		-19		dBm
$C/I_{1M,+2MHz}$	1 Mpsps mode, Adjacent (+2 MHz) interference		-42		dBm
$C/I_{1M,-3MHz}$	1 Mpsps mode, Adjacent (-3 MHz) interference		-38		dBm
$C/I_{1M,+3MHz}$	1 Mpsps mode, Adjacent (+3 MHz) interference		-48		dB
$C/I_{1M,\pm 6MHz}$	1 Mpsps mode, Adjacent (≥ 6 MHz) interference		-50		dB
$C/I_{1M BLE,co-channel}$	1 Mpsps BLE mode, Co-Channel interference		6		dB
$C/I_{1M BLE,-1MHz}$	1 Mpsps BLE mode, Adjacent (-1 MHz) interference		-2		dB
$C/I_{1M BLE,+1MHz}$	1Mpsps BLE mode, Adjacent (+1 MHz) interference		-9		dB
$C/I_{1M BLE,-2MHz}$	1Mpsps BLE mode, Adjacent (-2 MHz) interference		-22		dB
$C/I_{1M BLE,+2MHz}$	1Mpsps BLE mode, Adjacent (+2 MHz) interference		-46		dB
$C/I_{1M BLE,>3MHz}$	1Mpsps BLE mode, Adjacent (≥ 3 MHz) interference		-50		dB
$C/I_{1M BLE,image}$	Image frequency Interference -22 dB		-22		dB
$C/I_{1M BLE,image,1MHz}$	Adjacent (1 MHz) interference to in-band image frequency		-35		dB
$C/I_{2M,co-channel}$	2Mpsps mode, Co-Channel interference		10		dB
$C/I_{2M,-2MHz}$	2 Mpsps mode, Adjacent (-2 MHz) interference		6		dB
$C/I_{2M,+2MHz}$	2 Mpsps mode, Adjacent (+2 MHz) interference		-14		dB
$C/I_{2M,-4MHz}$	2 Mpsps mode, Adjacent (-4 MHz) interference		-20		dB
$C/I_{2M,+4MHz}$	2 Mpsps mode, Adjacent (+4 MHz) interference		-44		dB
$C/I_{2M,-6MHz}$	2 Mpsps mode, Adjacent (-6 MHz) interference		-42		dB

$C/I_{2M,+6MHz}$	2 Msps mode, Adjacent (+6 MHz) interference	-47	dB
$C/I_{2M,\geq 12MHz}$	2 Msps mode, Adjacent (≥ 12 MHz) interference	-52	dB
$C/I_{2MBLE,co-channel}$	2 Msps BLE mode, Co-Channel interference	7	dB
$C/I_{2MBLE,\pm 2MHz}$	2 Msps BLE mode, Adjacent (± 2 MHz) interference	0	dB
$C/I_{2MBLE,\pm 4MHz}$	2 Msps BLE mode, Adjacent (± 4 MHz) interference	-47	dB
$C/I_{2MBLE,\geq 6MHz}$	2 Msps BLE mode, Adjacent (≥ 6 MHz) interference	-49	dB
$C/I_{2MBLE,image}$	Image frequency Interference	-21	dB
$C/I_{2MBLE,image,2MHz}$	Adjacent (2 MHz) interference to in-band image frequency	-36	dB

3.3.8 RX intermodulation

Symbol	Description	Min.	Typ.	Max.	Units
$P_{IMD,1M}$	IMD performance, 1Msps (3MHz, 4MHz, and 5MHz offset)		-33		dBm
$P_{IMD,1M,BLE}$	IMD performance, BLE 1Msps (3MHz, 4MHz, and 5MHz offset)		-30		dBm
$P_{IMD,2M}$	IMD performance, 2Msps (6MHz, 8MHz, and 10MHz offset)		-33		dBm
$P_{IMD,2M,BLE}$	IMD performance, BLE 2Msps (6MHz, 8MHz, and 10MHz offset)		-32		dBm

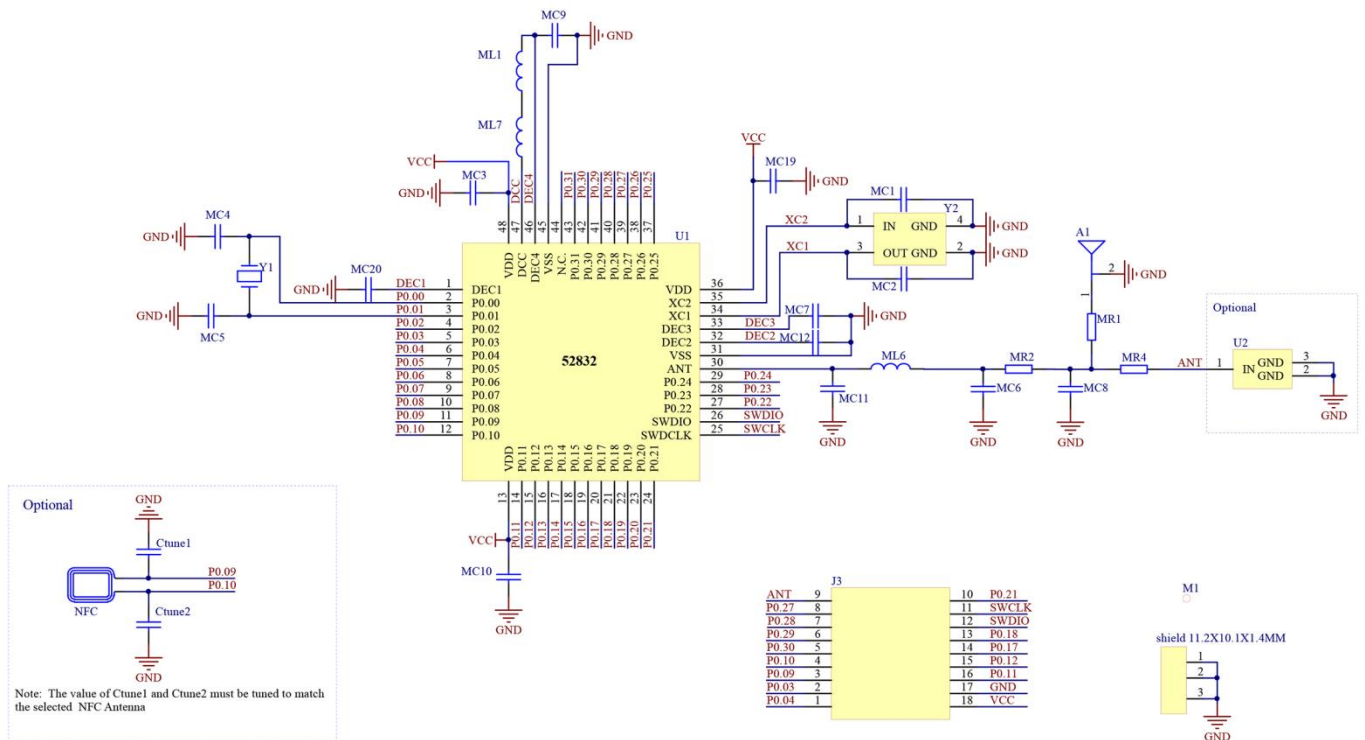
3.3.9 Radio timing

Symbol	Description	Min.	Typ.	Max.	Units
t_{TXEN}	Time between TXEN task and READY event after channel FREQUENCY configured		140		us
$t_{TXEN,FAST}$	Time between TXEN task and READY event after channel FREQUENCY configured (Fast Mode) FREQUENCY configured (Fast Mode)		40		us
$t_{TXDISABLE}$	Time between DISABLE task and DISABLED event when the radio was in TX and mode is set to 1Msps		6		us
$t_{TXDISABLE,2M}$	Time between DISABLE task and DISABLED event when the radio was in TX and mode is set to 2Msps		4		us
t_{RXEN}	Time between the RXEN task and READY event after channel FREQUENCY configured in default mode		140		us
$t_{RXEN,FAST}$	Time between the RXEN task and READY event after channel FREQUENCY configured in fast mode		40		us
t_{SWITCH}	The minimum time taken to switch from RX to TX or TX to RX (channel FREQUENCY unchanged)		20		us
$t_{RXDISABLE}$	Time between DISABLE task and DISABLED event when the radio was in RX		0		us
$t_{TXCHAIN}$	TX chain delay		0.6		us
$t_{RXCHAIN}$	RX chain delay		9.4		us
$t_{RXCHAIN,2M}$	RX chain delay in 2Msps mode		5		us

3.3.10 Received signal strength indicator (RSSI) specifications

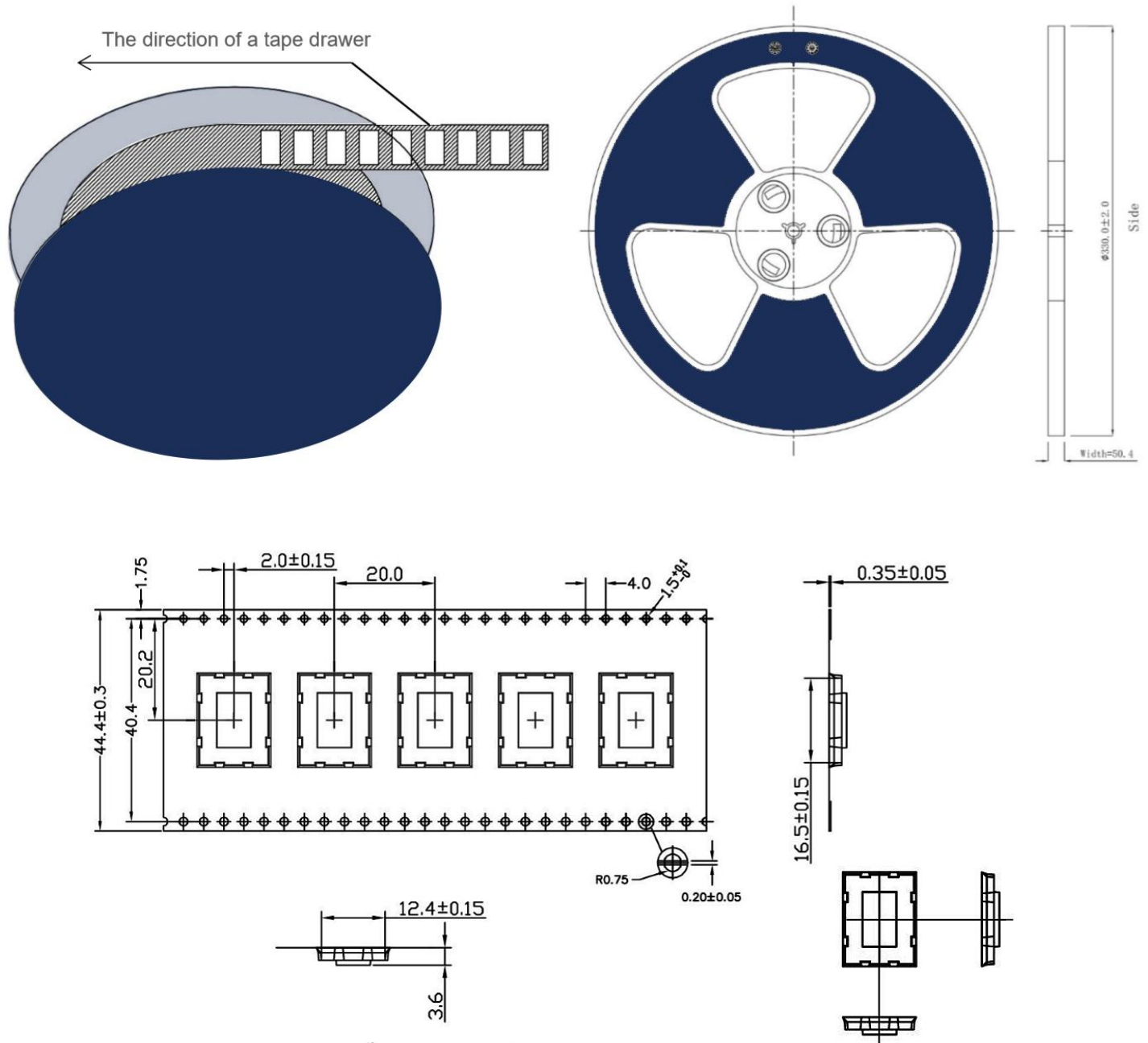
Symbol	Description	Min.	Typ.	Max.	Units
RSSI _{ACC}	RSSI Accuracy		±2		dB
RSSI _{RESOLUTION}	RSSI resolution		1		dB
RSSI _{PERIOD}	RSSI sampling time from RSSI_START task		0.25		μs
RSSI _{SETTLE}	RSSI settling time after signal level change		15		μs

4 Electrical Schematic



5 Package Information

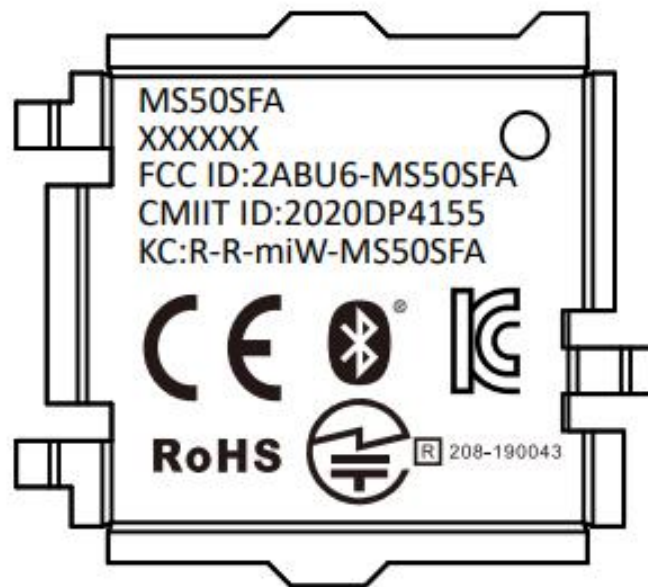
5.1 Package dimension



Details of Package Dimension:

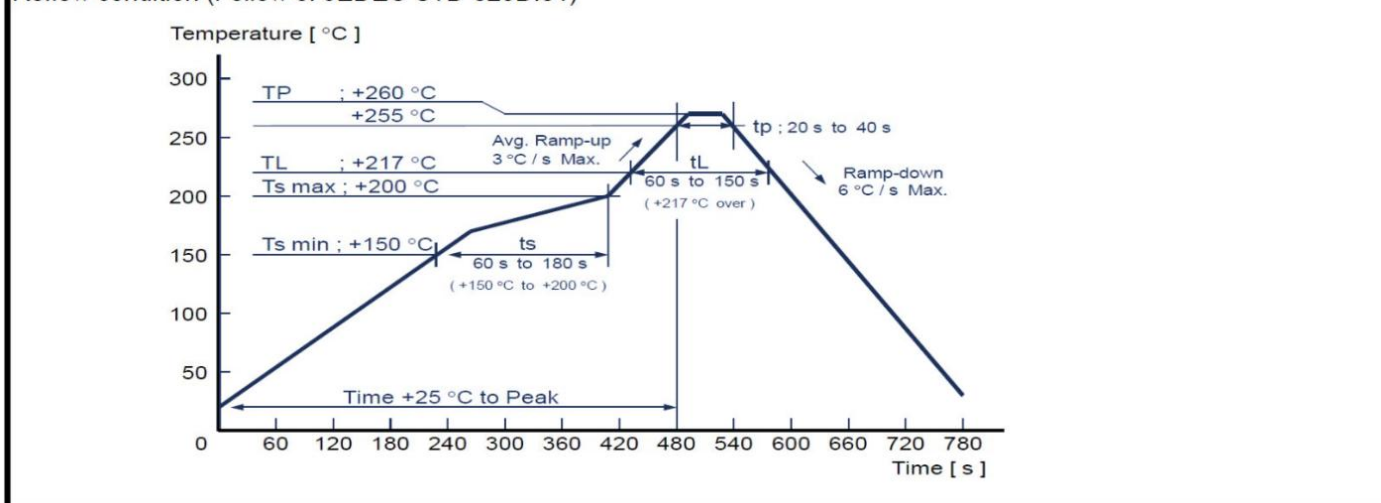
Details	Reel-MS50SFA
Quantity(module)	850PCS
Tape Weight	515g
Single module Weight	0.51g
Gross Weight	1000g
Dimension	W: 44mm T: 0.35mm

5.2 Mark on metal shield



6 Reflow and Soldering

Reflow condition (Follow of JEDEC STD-020D.01)



Profile Feature	Sn-Pb Assembly	Pb-Free Assembly
Solder Paste	Sn63/Pb37	Sn96.5/Ag3/Cu0.5
Preheat Temperature min (T _{smin})	100°C	150°C
Preheat Temperature max (T _{smax})	150°C	200°C
Preheat Time (T _{smin} to T _{smax})(t _s)	60-120 sec	60-120 sec
Average ramp-up rate (T _{smax} to T _p)	3°C/second max	3°C/second max
Liquidous Temperature (TL)	183°C	217°C
Time (t _L)Maintained Above (TL)	60-90 sec	30-90 sec
Peak Temperature (T _p)	220-235°C	230-250°C
Average ramp-down rate (T _p to T _{smax})	6°C/second max	6°C/second max
Time 25°C to peak temperature	6 minutes max	8 minutes max

Important:

- When SMT involves double-sided patch, it is recommended that the module surface be reflowed only once.
- For module SMT, it is recommended to make a partial stepped stencil with a thickness of 0.2mm, and the stencil hole should be extended by 0.8mm size.
- After opening the package, it should be stored in vacuum environment. Module should not be exposed to the air for a long time to prevent moisture and pad oxidation. If there is an interval of 7 to 30 days during SMT process, it is recommended to bake it with reel at 65-70 degrees for 24 hours before using for SMT again.

7 Certification

FCC ID: 2ABU6-MS50SFA

BQB QDID: 138541

TELEC:217-210105

KC: R-R-miW-MS50SFA

CE,RoHs,Reach certified

7.1 CE Certification

MS50SFA module is being tested and is expected to be compliant against the EU-Radio Equipment standards. OEM integrator should consult with qualified test house to verify all regulatory requirements have been met for their complete device.

7.2 FCC Certification

MS50SFA module is being tested and is expected to be compliant against the Federal Communications Commission standards.

As for the OEM integration:

Only OEM integrator have right to intend this device under the following conditions:

Any other transmitter or antenna must not be co-located with the antenna and transmitter. The module shall be only used with the integral antenna(s) that has been originally tested and certified with this module.

As long as the two conditions below are met, further transmitter testing will not be required.

(1) This device may not cause harmful interference.

(2) This device must accept any interference received, including interference that may cause undesired operation.

However, the OEM integrator shall test their end-product for any additional compliance requirements with this module installed (for example, digital device emission, PC peripheral requirements, etc.).

If these conditions cannot be met (for example certain laptop configuration or co-location with another transmitter), then the FCC authorization for this module in combination with the host equipment is no longer considered valid and the final product shall not use the FCC ID of the module. In these circumstances, the OEM integrator shall be re-evaluating the end product (including the transmitter) and obtaining a separate FCC authorization.

The OEM shall be verifying end product compliance with FCC Part 15, sub-part B limits for unintentional radiators through an accredited test facility.

7.3 Full Bluetooth Declaration ID

Minewsemi technologies meet the Bluetooth specification maintained by Bluetooth SIG, and all the product produced by Minewsemi is properly tested and comply with the Bluetooth license agreements.

Minewsemi is one of the associate member of Bluetooth SIG. The requirement of listing products by companies is become the members of the SIG and also pay the listed fees for each product required.

Please Kindly check the below Link to know more info:

<https://www.bluetooth.com/develop-with-bluetooth/qualification-listing>.

The Bluetooth Low Energy modules based on Nordic Semiconductor SoCs are listed as a “End product”.

7.4 Japan (TELEC)

The MS50SFA is approved for use in the Japanese market.

7.5 KC

The MS50SFA is approved for use in the Korean market.

7.6 Environmental

7.7 RoHs

MS50SFA modules are in compliance with Directive 2011/65/EU, 2015/863/EU of the European Parliament and the Council on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

7.8 Reach

MS50SFA modules listed below do not contain the 191 SVHC (Substance of Very High Concern), as defined by Directive EC/1907/2006 Article according to REACHAnnex XVII.

8 Notes & Cautions

We cannot assure that the specification has no errors and omission even though this specification is under collate and check strictly.

This specification is under the protection of laws and regulations of copyright, please do not copy and duplicate at any form, or do not transmit part or full of this specification in any wire and wireless network in any form, or do not edit or translate to any other format, word, code, etc.

8.1 Design notes

- It is critical to following the recommendations of this document to ensure the module meets the specifications.
- The module should be placed at the edge of the circuit board as far as possible to keep away from other circuits.
- Antenna should be kept away from other circuits. It can prevent low radiation efficiency and the normal use of other circuits from being affected.
- The landing of components should be appropriate and that is better for reducing the parasitic inductance.
- Please refuse to supply voltage that is not within the range of specification.
- Please make sure the module or its surface may not suffer from the physical shock or extreme stress.

8.2 Layout notes

To make sure wireless performance is at its best condition, please layout the MS50SFA module on the carrier board as below instructions and picture.

a) Placement of the antenna

The antenna area of module shall lay clearance completely and should not be blocked by the metal. Otherwise it will have effect on antenna performance (As the picture indicated below).

b) Placement of top-layer

The placement of top-layer in carrier board shall be lay copper completely to reduce the signal line in carrier board or other interference.

c) Clearance

The upper and below area of antenna (including the case) shall have 4mm or more than 4mm clearance to reduce the influences for antenna.



*The Grey area above is Carrier board.

8.3 Installation and soldering

Please do not lay copper under the module antenna. It can prevent the influence of signal radiation and the transmission distance from being affected.

8.4 Handling and storage

- a) Due to the fact that CMOS components are included in the module, it is better to eliminate static electricity at any methods when transporting or working with the module. Moreover, it is strongly recommended adding anti-ESD components to circuit design to hinder damage from real-life ESD events. Anti-ESD methods can be also used in mechanical design.



- b) Please store the modules within -40°C to $+125^{\circ}\text{C}$ before and after installation and make sure the modules is away from the direct sunlight exposure for a long duration. Modules should be far away from humid and salty air conditions, and any corrosive gasses or substances.
- c) Please not to wash the module. No-Clean Paste is used in production. The metal shield may be oxidized by the washing process and may lead to chemistry reaction with No-Clean Paste. If modules goes through the washing process, functions of the module may not guaranteed.
- d) After opening the package, it should be stored in vacuum environment. Module should not be exposed to the air for a long time to prevent moisture and pad oxidation. If there is an interval of 7 to 30 days during SMT process,

8.5 Life support applications

- a) The module is not design for life support device or system and not allowed to be used in destructive devices or system in any direct, or indirect ways. Minewsemi is not responsible for compensation of any losses when applying modules under such application as described above.
- b) Minewsemi shall not responsible for the customer's products or application.

9 Disclaimer

The factory has passed the ISO9001 quality management system, ISO14001 environmental management system and OAH18001 occupational health and safety assessment . Each product has been rigorously tested (transmission power test, sensitivity test, power consumption test, stability test, aging test, etc.).

* NOTICES:

- The Bluetooth trade mark is owned by the Bluetooth SIG Inc. USA.
- All other trademarks listed herein are owned by their respective owners.
- All specifications are subject to change without notice.
- Please do not use this specification for produce, sell or illegal purpose without MinewSemi's authorization.
- MinewSemi have right to interpret all the items above.

Revision History

Version	Date	Notes	Contributor(s)	Person of Approve
1.0	2022-03-01	First edition	Eddie	Coral

COPYRIGHT STATEMENT

This manual and all the contents contained in it are owned by Shenzhen Minewsemi Co., Ltd. and are protected by Chinese laws and applicable international conventions related to copyright laws.

The company has the right to change the content of this manual according to the technological development, and the revised version will not be notified otherwise. Without the written permission and authorization of the company, any individual, company, or organization shall not modify the contents of this manual or use part or all of the contents of this manual in other ways. Violators will be held accountable in accordance with the law.

MINEWSEMI

Tel: 0086-755-2801 0353

Email: minewsemi@minew.com

URL: <https://www.minew.com/>

Address: 3rd Floor, Building I, Gangzhilong Science Park, Qinglong Road Longhua District, Shenzhen 518109, China

